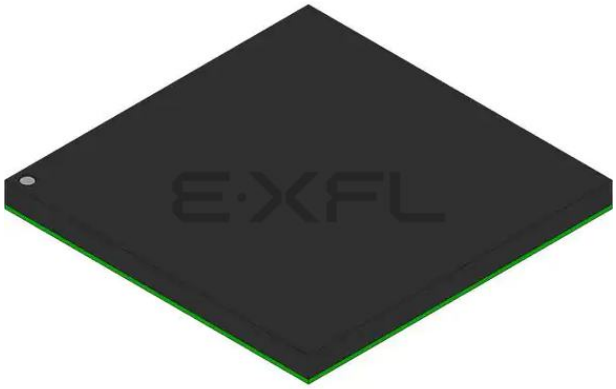

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	Coldfire V4E
Core Size	32-Bit Single-Core
Speed	266MHz
Connectivity	EBI/EMI, Ethernet, I²C, SPI, UART/USART, USB
Peripherals	DMA, PWM, WDT
Number of I/O	99
Program Memory Size	-
Program Memory Type	ROMless
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.43V ~ 1.58V
Data Converters	-
Oscillator Type	External
Operating Temperature	0°C ~ 70°C (TA)
Mounting Type	Surface Mount
Package / Case	388-BBGA
Supplier Device Package	388-PBGA (27x27)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mcf5475zp266

1 Maximum Ratings

Table 1 lists maximum and minimum ratings for supply and operating voltages and storage temperature. Operating outside of these ranges may cause erratic behavior or damage to the processor.

Table 1. Absolute Maximum Ratings

Rating	Symbol	Value	Units
External (I/O pads) supply voltage (3.3-V power pins)	EV_{DD}	–0.3 to +4.0	V
Internal logic supply voltage	IV_{DD}	–0.5 to +2.0	V
Memory (I/O pads) supply voltage (2.5-V power pins)	SD V_{DD}	–0.3 to +4.0 SDR Memory –0.3 to +2.8 DDR Memory	V
PLL supply voltage	PLL V_{DD}	–0.5 to +2.0	V
Internal logic supply voltage, input voltage level	V_{in}	–0.5 to +3.6	V
Storage temperature range	T_{stg}	–55 to +150	°C

2 Thermal Characteristics

2.1 Operating Temperatures

Table 2 lists junction and ambient operating temperatures.

Table 2. Operating Temperatures

Characteristic	Symbol	Value	Units
Maximum operating junction temperature	T_j	105	°C
Maximum operating ambient temperature	T_{Amax}	<70[1]	°C
Minimum operating ambient temperature	T_{Amin}	–0	°C

1 This published maximum operating ambient temperature should be used only as a system design guideline. All device operating parameters are guaranteed only when the junction temperature lies within the specified range.

2.2 Thermal Resistance

Table 3 lists thermal resistance values.

Table 3. Thermal Resistance

Characteristic		Symbol	Value	Unit
324 pin TEPBGA — Junction to ambient, natural convection	Four layer board (2s2p)	θ_{JMA}	20–22[1,2]	°C/W
388 pin TEPBGA — Junction to ambient, natural convection	Four layer board (2s2p)	θ_{JMA}	19[1,2]	°C/W

Table 3. Thermal Resistance (continued)

Characteristic		Symbol	Value	Unit
Junction to ambient (@200 ft/min)	Four layer board (2s2p)	θ_{JMA}	16[1,2]	°C/W
Junction to board	—	θ_{JB}	11[3]	°C/W
Junction to case	—	θ_{JC}	7[4]	°C/W
Junction to top of package	Natural convection	Ψ_{jt}	2[1,5]	°C/W

1 θ_{JA} and Ψ_{jt} parameters are simulated in accordance with EIA/JESD Standard 51-2 for natural convection. Freescale recommends the use of θ_{JA} and power dissipation specifications in the system design to prevent device junction temperatures from exceeding the rated specification. System designers should be aware that device junction temperatures can be significantly influenced by board layout and surrounding devices. Conformance to the device junction temperature specification can be verified by physical measurement in the customer's system using the Ψ_{jt} parameter, the device power dissipation, and the method described in EIA/JESD Standard 51-2.

2 Per JEDEC JESD51-6 with the board horizontal.

3 Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.

4 Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).

5 Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

3 DC Electrical Specifications

Table 4 lists DC electrical operating temperatures. This table is based on an operating voltage of EV_{DD} = 3.3 V_{DC} ± 0.3 V_{DC} and IV_{DD} of 1.5 ± 0.07 V_{DC}.

Table 4. DC Electrical Specifications

Characteristic	Symbol	Min	Max	Units
External (I/O pads) operation voltage range	EV_{DD}	3.0	3.6	V
Memory (I/O pads) operation voltage range (DDR Memory)	SD V_{DD}	2.30	2.70	V
Internal logic operation voltage range[1]	IV_{DD}	1.43	1.58	V
PLL Analog operation voltage range[1]	PLL V_{DD}	1.43	1.58	V
USB oscillator operation voltage range	USB_OSV_{DD}	3.0	3.6	V
USB digital logic operation voltage range	$USBV_{DD}$	3.0	3.6	V
USB PHY operation voltage range	USB_PHYV_{DD}	3.0	3.6	V
USB oscillator analog operation voltage range	USB_OSCAV_{DD}	1.43	1.58	V
USB PLL operation voltage range	USB_PLLV_{DD}	1.43	1.58	V
Input high voltage SSTL 3.3V/2.5V[2]	V_{IH}	V_{REF} + 0.3	SD V_{DD} + 0.3	V
Input low voltage SSTL 3.3V/2.5V[2]	V_{IL}	V_{SS} - 0.3	V_{REF} - 0.3	V
Input high voltage 3.3V I/O pins	V_{IH}	0.7 x EV_{DD}	EV_{DD} + 0.3	V
Input low voltage 3.3V I/O pins	V_{IL}	V_{SS} - 0.3	0.35 x EV_{DD}	V

Table 4. DC Electrical Specifications (continued)

Characteristic	Symbol	Min	Max	Units
Output high voltage I_{OH} = 8 mA, 16 mA,24 mA	V_{OH}	2.4	—	V
Output low voltage I_{OL} = 8 mA, 16 mA,24 mA[5]	V_{OL}	—	0.5	V
Capacitance [3], V_{in} = 0 V, f = 1 MHz	C_{IN}	—	TBD	pF
Input leakage current	I_{in}	–1.0	1.0	µA

1 IV_{DD} and PLL V_{DD} should be at the same voltage. PLL V_{DD} should have a filtered input. Please see Figure 2 for an example circuit. There are three PLL V_{DD} inputs. A filter circuit should used on each PLL V_{DD} input.

2 This specification is guaranteed by design and is not 100% tested.

3 Capacitance C_{IN} is periodically sampled rather than 100% tested.

4 Hardware Design Considerations

4.1 PLL Power Filtering

To further enhance noise isolation, an external filter is strongly recommended for PLL analog V_{DD} pins. The filter shown in Figure 2 should be connected between the board V_{DD} and the PLL V_{DD} pins. The resistor and capacitors should be placed as close to the dedicated PLL V_{DD} pin as possible.

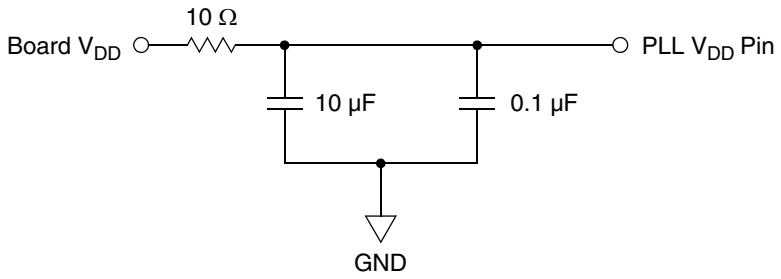
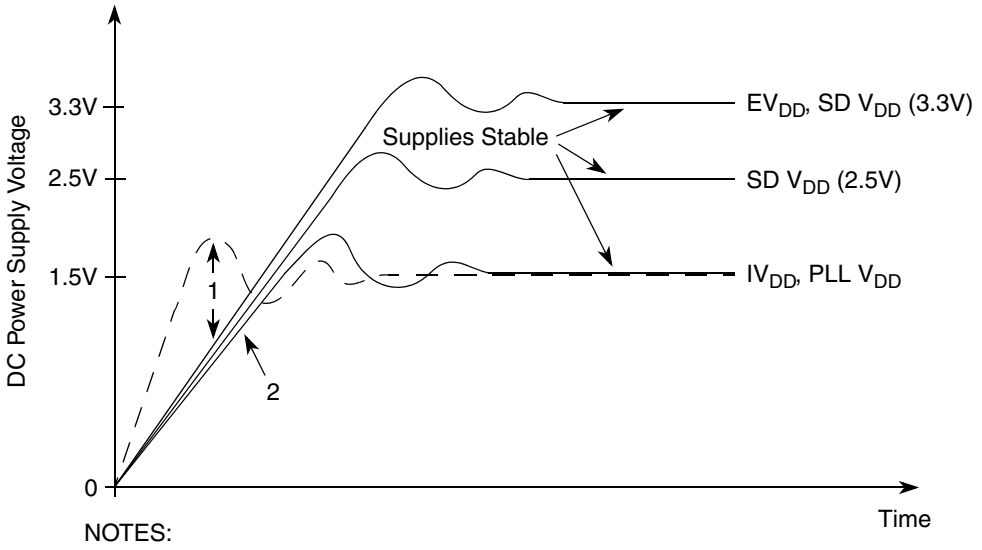


Figure 2. System PLL V_{DD} Power Filter

4.2 Supply Voltage Sequencing and Separation Cautions

Figure 3 shows situations in sequencing the I/O V_{DD} (EV_{DD}), SDRAM V_{DD} (SD V_{DD}), PLL V_{DD} (PLL V_{DD}), and Core V_{DD} (IV_{DD}).



NOTES:
1. IVDD should not exceed EVDD or SD VDD by more than 0.4V at any time, including power-up.
2. Recommended that IVDD/PLL VDD should track EVDD/SD VDD up to 0.9V, then separate for completion of ramps.
3. Input voltage must not be greater than the supply voltage (EVDD, SD VDD, IVDD, or PLL VDD) by more than 0.5V at any time, including during power-up.
4. Use 1 microsecond or slower rise time for all supplies.

Figure 3. Supply Voltage Sequencing and Separation Cautions

The relationship between SD V_{DD} and EV_{DD} is non-critical during power-up and power-down sequences. SD V_{DD} (2.5V or 3.3V) and EV_{DD} are specified relative to IV_{DD}.

4.2.1 Power Up Sequence

If EV_{DD}/SD V_{DD} are powered up with the IV_{DD} at 0V, the sense circuits in the I/O pads cause all pad output drivers connected to the EV_{DD}/SD V_{DD} to be in a high impedance state. There is no limit to how long after EV_{DD}/SD V_{DD} powers up before IV_{DD} must power up. IV_{DD} should not lead the EV_{DD}, SD V_{DD}, or PLL V_{DD} by more than 0.4V during power ramp up or there is high current in the internal ESD protection diodes. The rise times on the power supplies should be slower than 1 microsecond to avoid turning on the internal ESD protection clamp diodes.

The recommended power up sequence is as follows:

1. Use 1 microsecond or slower rise time for all supplies.
2. IV_{DD}/PLL V_{DD} and EV_{DD}/SD V_{DD} should track up to 0.9V, then separate for the completion of ramps with EV_{DD}/SD V_{DD} going to the higher external voltages. One way to accomplish this is to use a low drop-out voltage regulator.

4.2.2 Power Down Sequence

If IV_{DD}PLL V_{DD} are powered down first, sense circuits in the I/O pads cause all output drivers to be in a high impedance state. There is no limit on how long after IV_{DD} and PLL V_{DD} power down before EV_{DD} or SD V_{DD} must power down. IV_{DD} should not lag EV_{DD}, SD V_{DD}, or PLL V_{DD} going low by more than 0.4V during power down or there is undesired high current in the ESD protection diodes. There are no requirements for the fall times of the power supplies.

The recommended power down sequence is as follows:

1. Drop IV_{DD}/PLL V_{DD} to 0V
2. Drop EV_{DD}/SD V_{DD} supplies

4.4 USB Power Filtering

To minimize noise, an external filter is required for each of the USB power pins. The filter shown in Figure 6 should be connected between the board EV_{DD} or IV_{DD} and each of the USB V_{DD} pins.

- The resistor and capacitors should be placed as close to the dedicated USB V_{DD} pin as possible.
- A separate filter circuit should be included for each USB V_{DD} pin, a total of five circuits.
- All traces should be as low impedance as possible, especially ground pins to the ground plane.
- The filter for USB_PHYVDD to VSS should be connected to the power and ground planes, respectively, not fingers of the planes.
- In addition to keeping the filter components for the USB_PLLVDD as close as practical to the body of the processor as previously mentioned, special care should be taken to avoid coupling switching power supply noise or digital switching noise onto the portion of that supply between the filter and the processor.
- The capacitors for C2 in the table below should be rated X5R or better due to temperature performance.

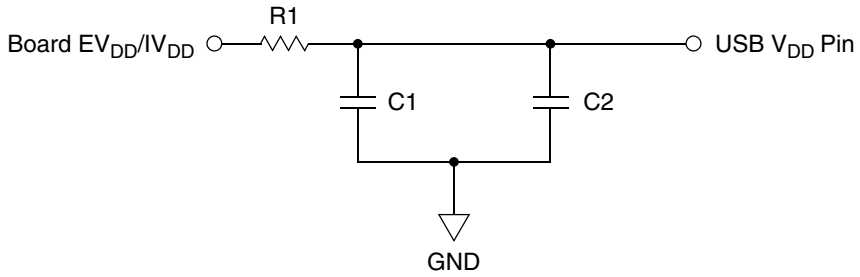


Figure 6. USB V_{DD} Power Filter

NOTE

In addition to the above filter circuitry, a 0.01 F capacitor is also recommended in parallel with those shown.

Table 5 lists the resistor values and supply voltages to be used in the circuit for each of the USB V_{DD} pins.

Table 5. USB Filter Circuit Values

USB V_{DD} Pin	Nominal Voltage	R1 (Ω)	C1 (μF)	C2 (μF)
USBVDD (Bias generator supply)	3.3V	10	10	0.1
USB_PHYVDD (Main transceiver supply)	3.3V	0	10	0.1
USB_PLLVDD (PLL supply)	1.5V	10	1	0.1
USB_OSCVDD (Oscillator supply)	3.3V	0	10	0.1
USB_OSCAVDD (Oscillator analog supply)	1.5V	0	10	0.1

4.4.1 Bias Resistor

The USBRBIAS resistor should be placed as close to the dedicated USB 2.0 pins as possible. The tolerance should be ±1%.

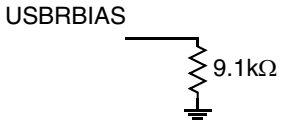


Figure 7. USBRBIAS Connection

5 Output Driver Capability and Loading

Table 6 lists values for drive capability and output loading.

Table 6. I/O Driver Capability[1]

Signal	Drive Capability	Output Load (C_L)
SDRAMC (SDADDR[12:0], SDDATA[31:0], $\overline{\text{RAS}}$, $\overline{\text{CAS}}$, SDDM[3:0], $\overline{\text{SDWE}}$, SDBA[1:0]	24 mA	15 pF
SDRAMC DQS and clocks (SDDQS[3:0], SDRDQS, SDCLK[1:0], $\overline{\text{SDCLK}}$[1:0], SDCKE)	24 mA	15 pF
SDRAMC chip selects ($\overline{\text{SDCS}}$[3:0])	24 mA	15 pF
FlexBus (AD[31:0], $\overline{\text{FBCS}}$[5:0], ALE, R/$\overline{\text{W}}$, $\overline{\text{BE}}$/$\overline{\text{BWE}}$[3:0], $\overline{\text{OE}}$)	16 mA	30 pF
FEC (E*n*MDIO, E*n*MDC, E*n*TXEN, E*n*TXD[3:0], E*n*TXER	8 mA	15 pF
Timer (TOUT[3:0])	8 mA	50 pF
$\overline{\text{DACK}}$[1:0]	8 mA	30 pF
PSC (PSC*n*TXD[3:0], $\overline{\text{PSC}n\text{RTS}}$/PSC*n*FSYNC,	8 mA	30 pF
DSPI (DSPISOUT, DSPICS0/SS, DSPICS[2:3], DSPICS5/PCSS)	24 mA	50 pF
PCI (PCIAD[31:0], PCIBG[4:1], PCIBG0/PCIREQOUT, PCIDEVSEL, PCICXBE[3:0], PCIFRM, PCIPERR, PCIRESET, PCISERR, PCISTOP, PCIPAR, PCITRDY, PCIIRDY	16 mA	50 pF
I2C (SCL, SDA)	8 mA	50 pF
BDM (PSTCLK, PSTDDATA[7:0], DSO/TDO,	8 mA	25 pF
RSTO	8 mA	50 pF

[1] The device's pads have balanced sink and source current. The drive capability is the same as the sink capability.

6 PLL Timing Specifications

The specifications in Table 7 are for the CLKIN pin.

Table 7. Clock Timing Specifications

Num	Characteristic	Min	Max	Units
C1	Cycle time	15.0	40	ns
C2	Rise time (20% of Vdd to 80% of vdd)	—	2	ns
C3	Fall time (80% of Vdd to 20% of Vdd)	—	2	ns
C4	Duty cycle (at 50% of Vdd)	40	60	%

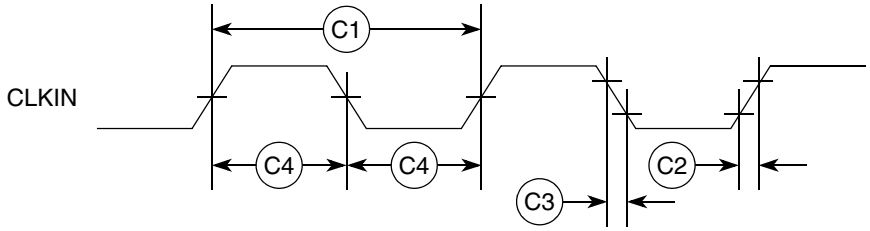


Figure 8. Input Clock Timing Diagram

Table 8 shows the supported PLL encodings.

Table 8. MCF547x Divide Ratio Encodings

AD[12:8][1]	Clock Ratio	CLKIN—PCI and FlexBus Frequency Range (MHz)	Internal XLB, SDRAM Bus, and PSTCLK Frequency Range (MHz)	Core Frequency Range (MHz)
00011	1:2	41.67–66.66	83.33–133.33	166.66–266.66
00101	1:2	25.0–44.42	50.0–88.83[2]	100.0–177.66
01111	1:4	25.0–33.3	100–133.33	200–266.66

1 All other values of AD[12:8] are reserved.

2 DDR memories typically have a minimum speed of 83 MHz. Some vendors specifiy down to 75 MHz. Check with the memory component specifications to verify.

Figure 9 correlates CLKIN, internal bus, and core clock frequencies for the 1x–4x multipliers.

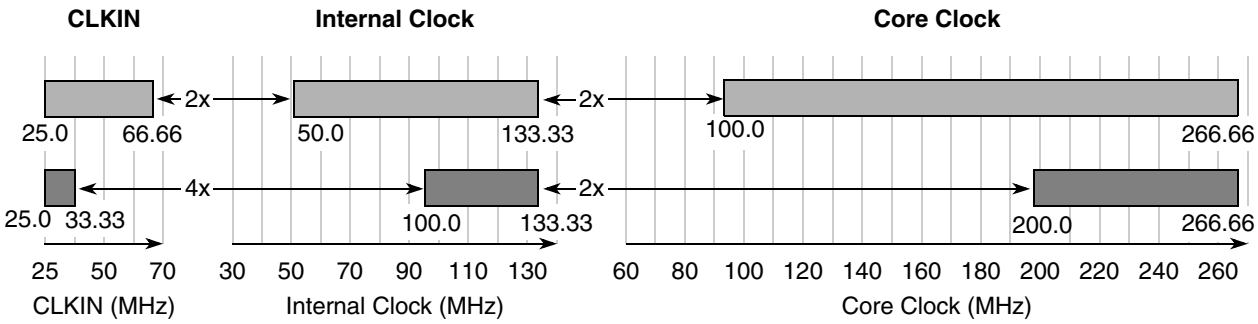


Figure 9. CLKIN, Internal Bus, and Core Clock Ratios

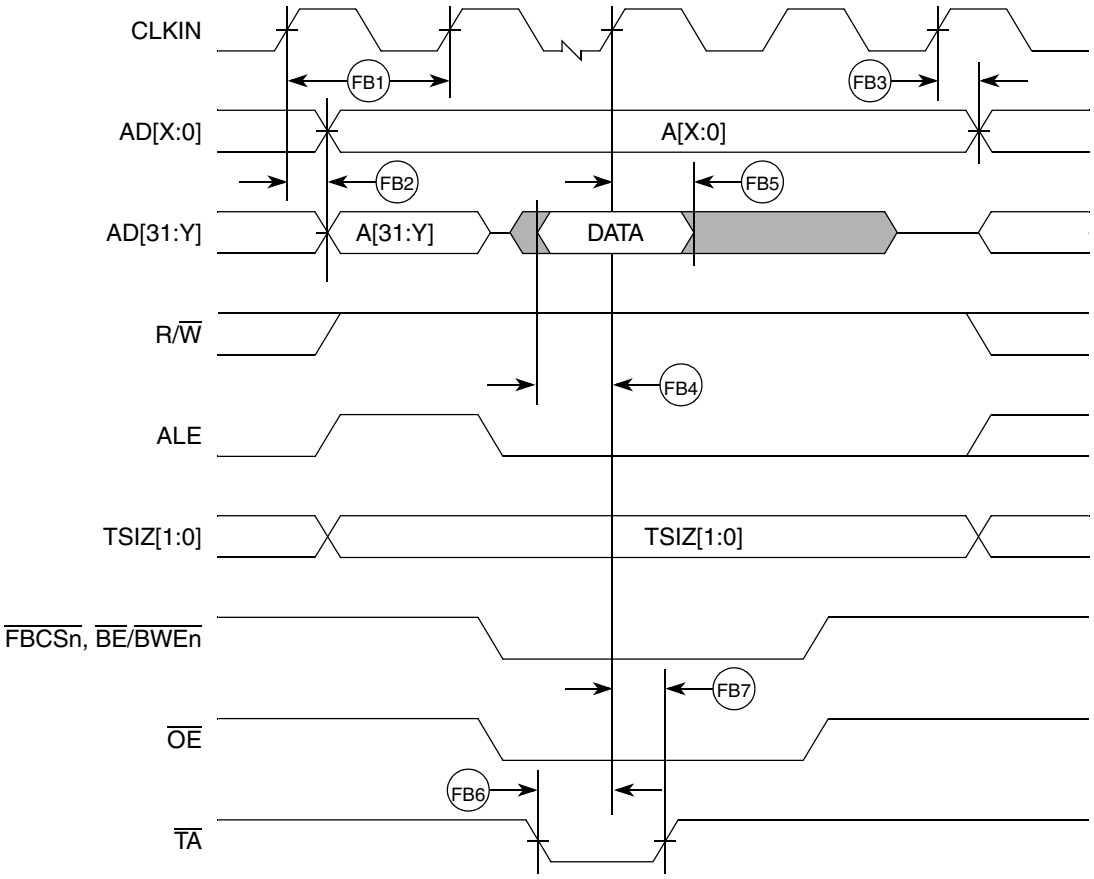


Figure 11. FlexBus Read Timing

Table 11. SDR Timing Specifications

Symbol	Characteristic	Min	Max	Unit	Notes
	Frequency of Operation	0	133	Mhz	1
SD1	Clock Period (t_{CK})	7.52	12	ns	2
SD2	Clock Skew (t_{SK})		TBD		
SD3	Pulse Width High (t_{CKH})	0.45	0.55	SDCLK	3
SD4	Pulse Width Low (t_{CKL})	0.45	0.55	SDCLK	4
SD5	Address, CKE, CAS, RAS, WE, BA, CS - Output Valid (t_{CMV})		0.5 × SDCLK + 1.0ns	ns	
SD6	Address, CKE, CAS, RAS, WE, BA, CS - Output Hold (t_{CMH})	2.0		ns	
SD7	SDRDQS Output Valid (t_{DQSOV})		Self timed	ns	5
SD8	SDDQS[3:0] input setup relative to SDCLK (t_{DQSIS})	0.25 × SDCLK	0.40 × SDCLK	ns	6
SD9	SDDQS[3:0] input hold relative to SDCLK (t_{DQSIH})	Does not apply. 0.5 SDCLK fixed width.			7
SD10	Data Input Setup relative to SDCLK (reference only) (t_{DIS})	0.25 × SDCLK		ns	8
SD11	Data Input Hold relative to SDCLK (reference only) (t_{DIH})	1.0		ns	
SD12	Data and Data Mask Output Valid (t_{DV})		0.75 × SDCLK +0.500ns	ns	
SD13	Data and Data Mask Output Hold (t_{DH})	1.5		ns	

1 The frequency of operation is 2x or 4x the CLKIN frequency of operation. The MCF547X supports a single external reference clock (CLKIN). This signal defines the frequency of operation for FlexBus and PCI, but SDRAM clock operates at the same frequency as the internal bus clock. Please see the PLL chapter of the *MCF547X Reference Manual* for more information on setting the SDRAM clock rate.

2 SDCLK is one SDRAM clock in (ns).

3 Pulse width high plus pulse width low cannot exceed min and max clock period.

4 Pulse width high plus pulse width low cannot exceed min and max clock period.

5 SDR_DQS is designed to pulse 0.25 clock before the rising edge of the memory clock. This is a guideline only. Subtle variation from this guideline is expected. SDR_DQS only pulses during a read cycle and one pulse occurs for each data beat.

6 SDR_DQS is designed to pulse 0.25 clock before the rising edge of the memory clock. This spec is a guideline only. Subtle variation from this guideline is expected. SDR_DQS only pulses during a read cycle and one pulse occurs for each data beat.

7 The SDR_DQS pulse is designed to be 0.5 clock in width. The timing of the rising edge is most important. The falling edge does not affect the memory controller.

8 Because a read cycle in SDR mode uses the DQS circuit within the MCF547X, it is most critical that the data valid window be centered 1/4 clk after the rising edge of DQS. Ensuring that this happens results in successful SDR reads. The input setup spec is provided as guidance.

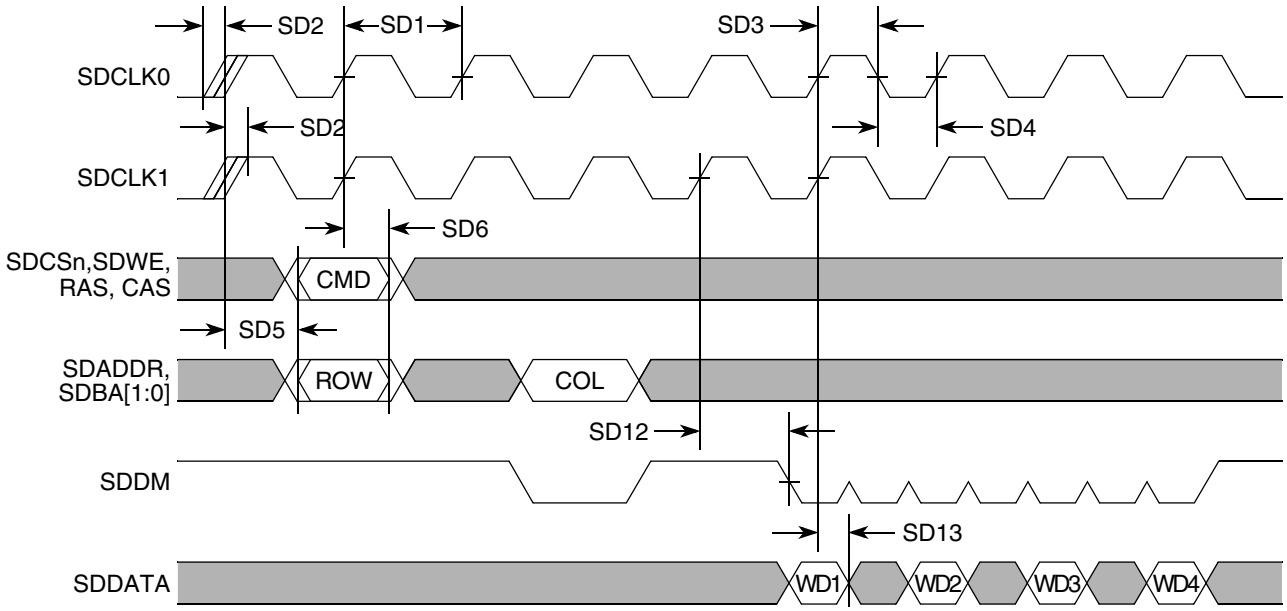


Figure 13. SDR Write Timing

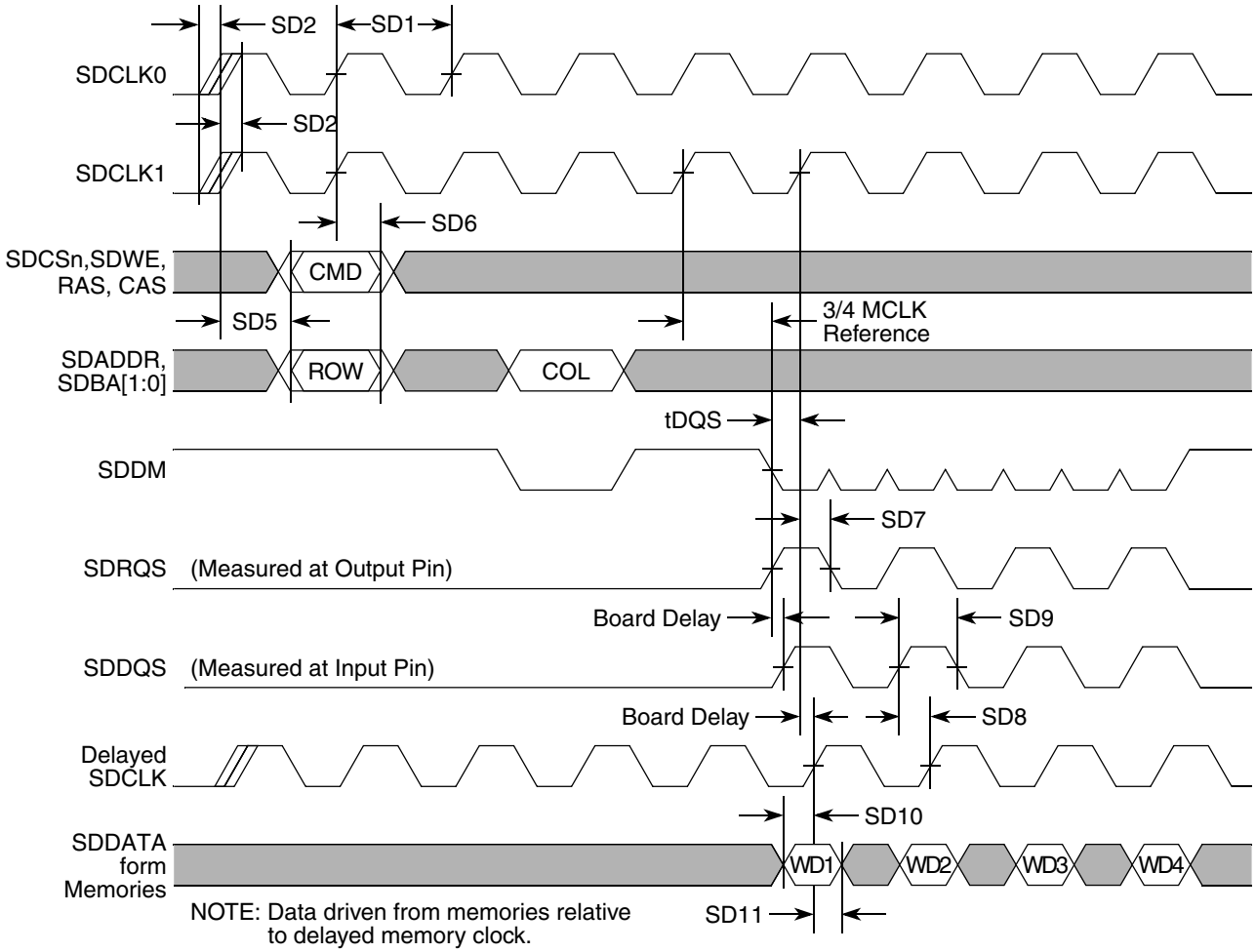


Figure 14. SDR Read Timing

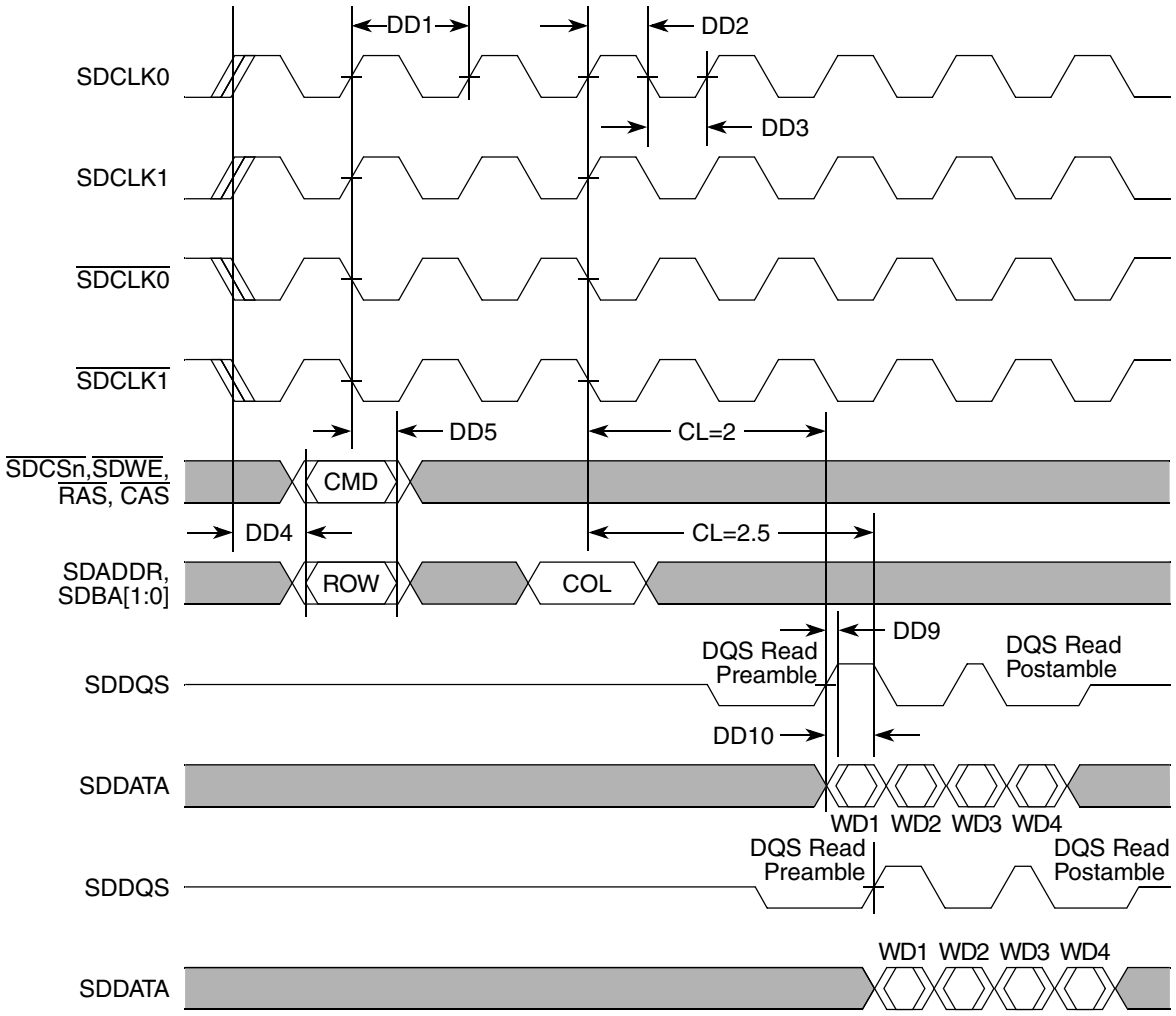


Figure 17. DDR Read Timing

10 PCI Bus

The PCI bus on the MCF547*x* is PCI 2.2 compliant. The following timing numbers are mostly from the PCI 2.2 spec. Please refer to the PCI 2.2 spec for a more detailed timing analysis.

Table 14. PCI Timing Specifications

Num	Characteristic	Min	Max	Unit	Notes
	Frequency of Operation	25	66	MHz	1
P1	Clock Period (t_{CK})	15.15	40	ns	2
P2	Address, Data, and Command (33< PCI ≤ 66 Mhz)—Input Setup (t_{IS})	3.0	—	ns	
P3	Address, Data, and Command (0 < PCI ≤ 33 Mhz)—Input Setup (t_{IS})	7.0	—	ns	
P4	Address, Data, and Command (33–66 Mhz)—Output Valid (t_{DV})	—	6.0	ns	3
P5	Address, Data, and Command (0–33 Mhz) - Output Valid (t_{DV})	—	11.0	ns	
P6	PCI signals (0–66 Mhz) - Output Hold (t_{DH})	0	—	ns	4

Table 15. MII Receive Signal Timing

Num	Characteristic	Min	Max	Unit
M1	RXD[3:0], RXDV, RXER to RXCLK setup	5	—	ns
M2	RXCLK to RXD[3:0], RXDV, RXER hold	5	—	ns
M3	RXCLK pulse width high	35%	65%	RXCLK period
M4	RXCLK pulse width low	35%	65%	RXCLK period

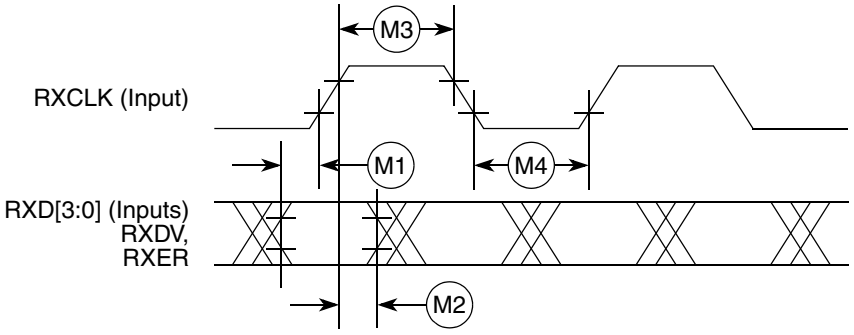


Figure 19. MII Receive Signal Timing Diagram

11.2 MII Transmit Signal Timing

Table 16. MII Transmit Signal Timing

Num	Characteristic	Min	Max	Unit
M5	TXCLK to TXD[3:0], TXEN, TXER invalid	0	—	ns
M6	TXCLK to TXD[3:0], TXEN, TXER valid	—	25	ns
M7	TXCLK pulse width high	35%	65%	TXCLK period
M8	TXCLK pulse width low	35%	65%	TXCLK period

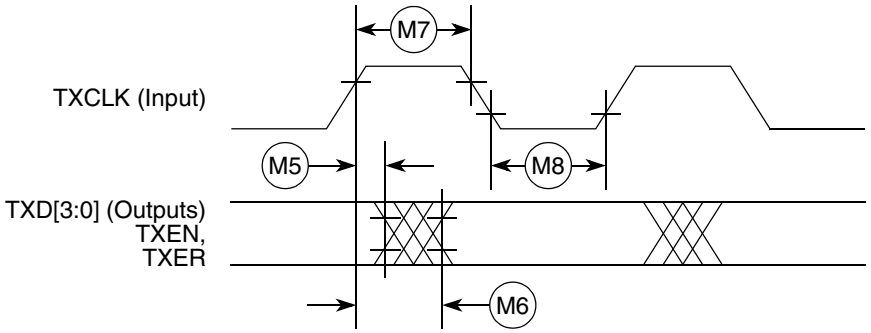


Figure 20. MII Transmit Signal Timing Diagram

1 Output numbers depend on the value programmed into the IFDR; an IFDR programmed with the maximum frequency (IFDR = 0x20) results in minimum output timings as shown in Table 21. The I^2C interface is designed to scale the actual data transition time to move it to the middle of the SCL low period. The actual position is affected by the prescale and division values programmed into the IFDR; however, the numbers given in Table 21 are minimum values.

2 Because SCL and SDA are open-collector-type outputs, which the processor can only actively drive low, the time SCL or SDA take to reach a high level depends on external signal capacitance and pull-up resistor values.

3 Specified at a nominal 50-pF load.

Figure 23 shows timing for the values in Table 20 and Table 21.

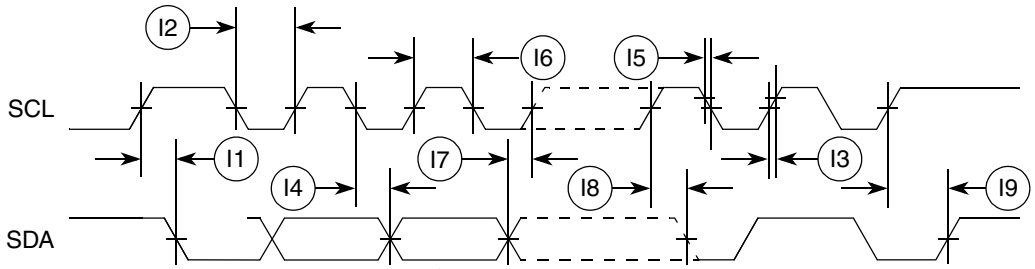


Figure 23. I^2C Input/Output Timings

14 JTAG and Boundary Scan Timing

Table 22. JTAG and Boundary Scan Timing

Num	Characteristics[1]	Symbol	Min	Max	Unit
J1	TCLK Frequency of Operation	f_{JCYC}	DC	10	MHz
J2	TCLK Cycle Period	t_{JCYC}	2	—	t_{CK}
J3	TCLK Clock Pulse Width	t_{JCW}	15.15	—	ns
J4	TCLK Rise and Fall Times	t_{JCRF}	0.0	3.0	ns
J5	Boundary Scan Input Data Setup Time to TCLK Rise	t_{BSDST}	5.0	—	ns
J6	Boundary Scan Input Data Hold Time after TCLK Rise	t_{BSDHT}	24.0	—	ns
J7	TCLK Low to Boundary Scan Output Data Valid	t_{BSDV}	0.0	15.0	ns
J8	TCLK Low to Boundary Scan Output High Z	t_{BSDZ}	0.0	15.0	ns
J9	TMS, TDI Input Data Setup Time to TCLK Rise	t_{TAPBST}	5.0	—	ns
J10	TMS, TDI Input Data Hold Time after TCLK Rise	t_{TAPBHT}	10.0	—	ns
J11	TCLK Low to TDO Data Valid	t_{TDODV}	0.0	20.0	ns
J12	TCLK Low to TDO High Z	t_{TDODZ}	0.0	15.0	ns
J13	$\overline{TRST}$ Assert Time	t_{TRSTAT}	100.0	—	ns
J14	$\overline{TRST}$ Setup Time (Negation) to TCLK High	t_{TRSTST}	10.0	—	ns

1 MTMOD is expected to be a static signal. Hence, it is not associated with any timing

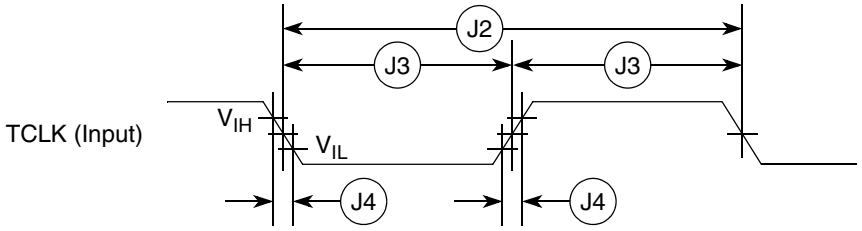


Figure 24. Test Clock Input Timing

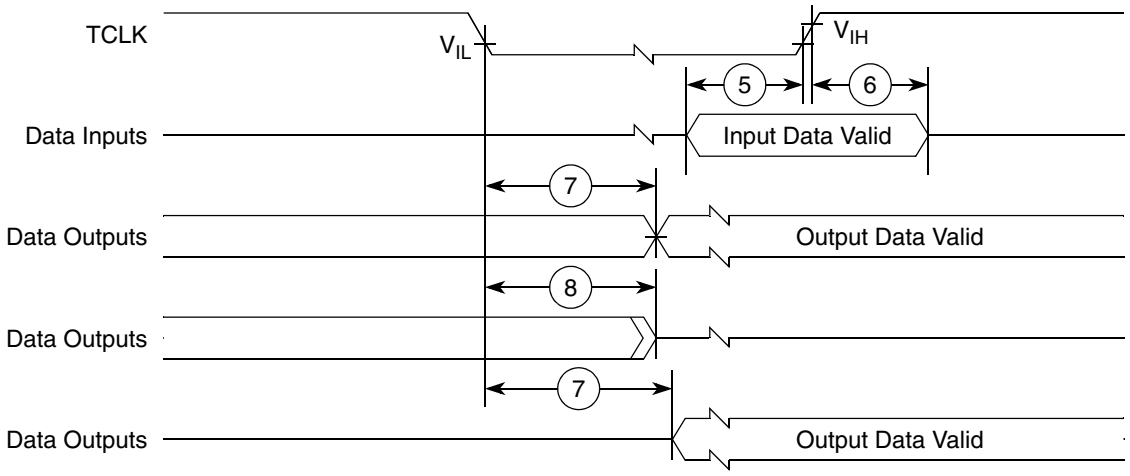


Figure 25. Boundary Scan (JTAG) Timing

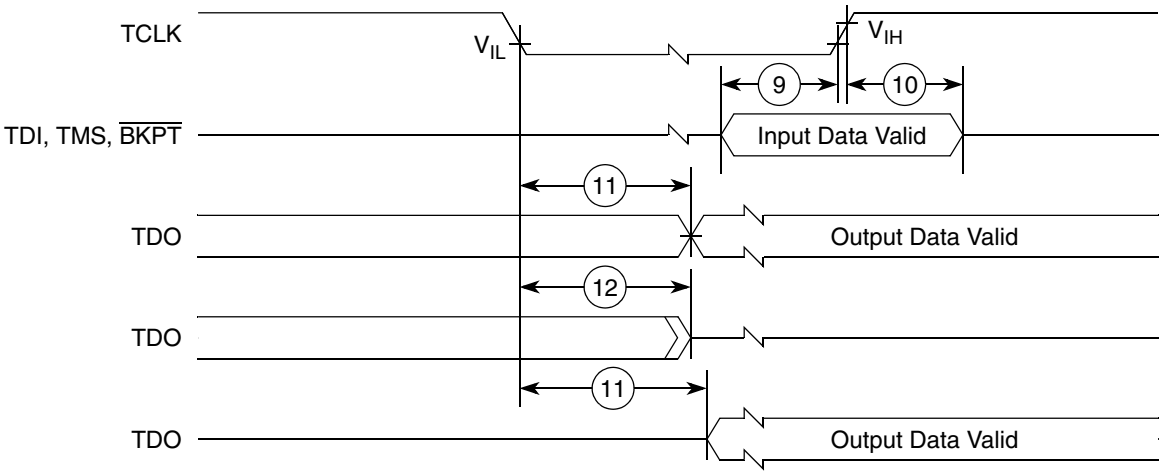


Figure 26. Test Access Port Timing

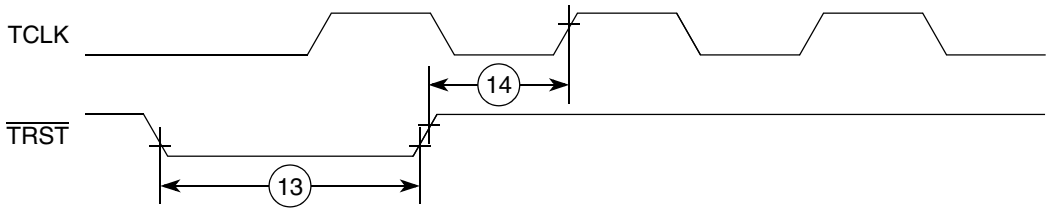


Figure 27. TRST Timing Debug AC Timing Specifications

Table 23 lists specifications for the debug AC timing parameters shown in Figure 29.

Table 23. Debug AC Timing Specifications

Num	Characteristic	66 MHz		Units
		Min	Max	
D1	PSTDDATA to PSTCLK setup	4.5	—	ns
D2	PSTCLK to PSTDDATA hold	4.5	—	ns
D3	DSI-to-DSCLK setup	1	—	PSTCLKs
D4 [1]	DSCLK-to-DSO hold	4	—	PSTCLKs
D5	DSCLK cycle time	5	—	PSTCLKs

[1] DSCLK and DSI are synchronized internally. D4 is measured from the synchronized DSCLK input relative to the rising edge of CLKOUT.

Figure 28 shows real-time trace timing for the values in Table 23.

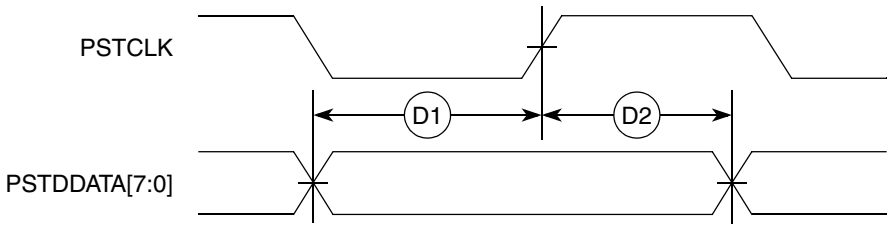


Figure 28. Real-Time Trace AC Timing

Figure 29 shows BDM serial port AC timing for the values in Table 23.

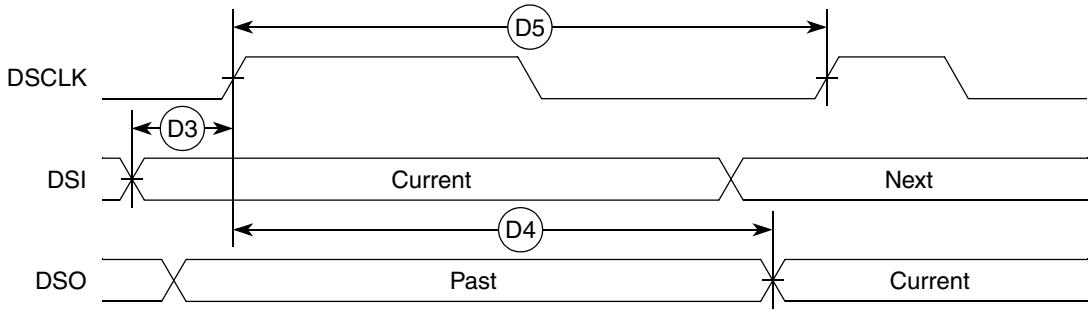


Figure 29. BDM Serial Port AC Timing

15 DSPI Electrical Specifications

Table 24 lists DSPI timings.

Table 24. DSPI Modules AC Timing Specifications

Name	Characteristic	Min	Max	Unit
DS1	DSPI_CS[3:0] to DSPI_CLK	1 × tck	510 × tck	ns
DS2	DSPI_CLK high to DSPI_DOUT valid.	—	12	ns
DS3	DSPI_CLK high to DSPI_DOUT invalid. (Output hold)	2	—	ns
DS4	DSPI_DIN to DSPI_CLK (Input setup)	10	—	ns
DS5	DSPI_DIN to DSPI_CLK (Input hold)	10	—	ns

The values in Table 24 correspond to Figure 30.

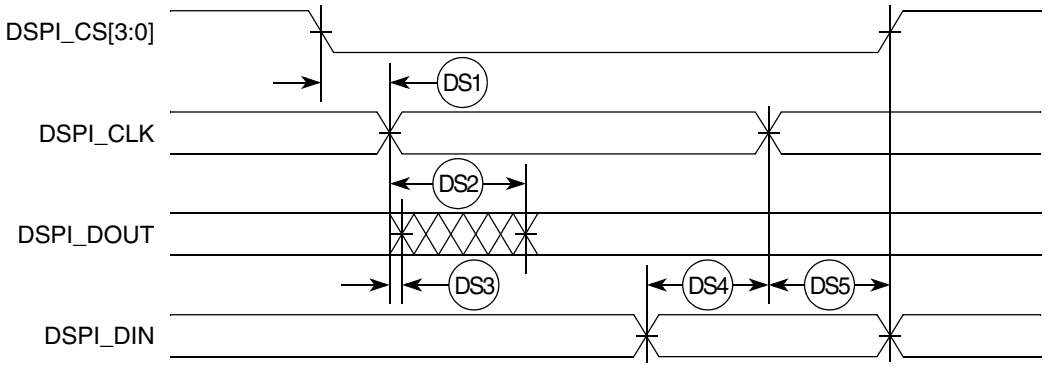


Figure 30. DSPI Timing

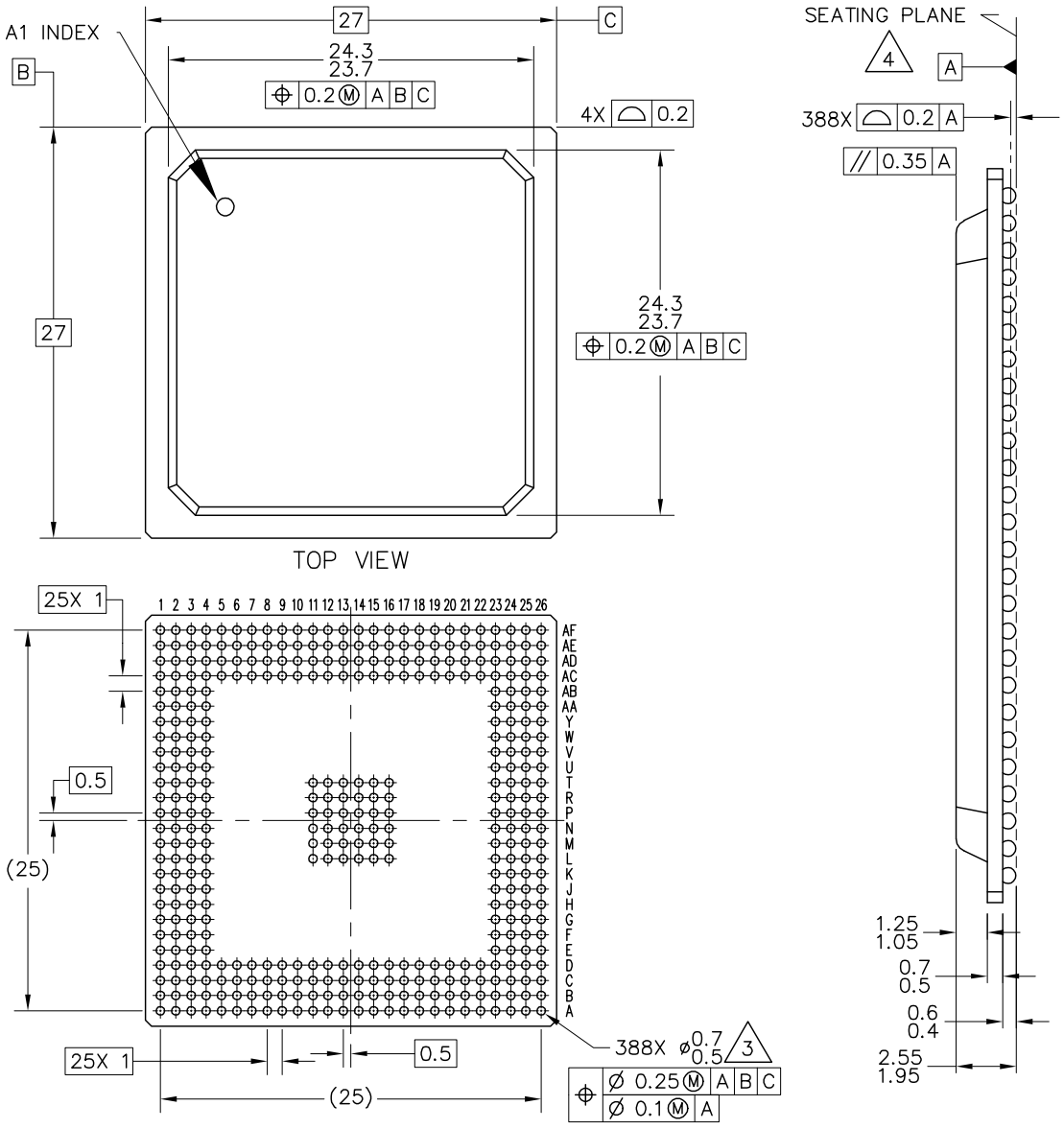
16 Timer Module AC Timing Specifications

Table 25 lists timer module AC timings.

Table 25. Timer Module AC Timing Specifications

Name	Characteristic	0–66 MHz		Unit
		Min	Max	
T1	TIN0 / TIN1 / TIN2 / TIN3 cycle time	3	—	PSTCLK
T2	TIN0 / TIN1 / TIN2 / TIN3 pulse width	1	—	PSTCLK

17 Case Drawing



MECHANICAL OUTLINE	PRINT VERSION NOT TO SCALE

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388 I/O, PBGA 27 X 27 PKG, 1 MM PITCH (OMPAC)	CASE NUMBER: 1164–02	25 JAN 2007
	STANDARD: JEDEC MS–034 AAL–1	

NOTES:

1. ALL DIMENSIONS IN MILLIMETERS.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M–1994.
3. MAXIMUM SOLDER BALL DIAMETER MEASURED PARALLEL TO DATUM A.
4. DATUM A, THE SEATING PLANE, IS DETERMINED BY THE SPHERICAL CROWNS OF THE SOLDER BALLS.
5. PACKAGE CODES:
   5254 – 2 LAYER SUBSTRATE PACKAGE
   5367 – 4 LAYER SUBSTRATE PACKAGE

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	CASE NUMBER: 1164–02	25 JAN 2007
	STANDARD: JEDEC MS–034 AAL–1	

Figure 31. 388-pin BGA Case Outline

18 Revision History

Revision Number	Date	Substantive Changes
2.2	August 29, 2005	Table 7: Changed C1 maximum spec from 33.3 ns to 40 ns.
2.3	August 30, 2005	Table 22: Changed J11 maximum from 15 ns to 20 ns.
2.4	December 14, 2005	Table 10: Changed FB1 maximum from 33.33 ns to 40 ns. Table 14: Changed FB1 maximum from 33.33 ns to 40 ns.
3	February 20, 2007	Table 4: Updated DC electrical specifications, V_{IL} and V_{IH}. Table 6: Changed FlexBus output load from 20pF to 30pF. Added Section 4.3, “General USB Layout Guidelines.”
4	December 4, 2007	Figure 2: Changed resistor value from 10W to 10Ω Figure 3: Changed note 1 in from “IVDD should not exceed EVDD, SD VDD or PLL VDD by more than 0.4V...” to “IVDD should not exceed EVDD or SD VDD by more than 0.4V...” Table 3: Updated thermal information for θ_{JMA}, θ_{JB}, and θ_{JC} Table 4: Added input leakage current spec. Table 6: Added footnote regarding pads having balanced source & sink current. Table 9: Added $\overline{\text{RSTI}}$ pulse duration spec. Added features list, pinout drawing, block diagram, and case outline.

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